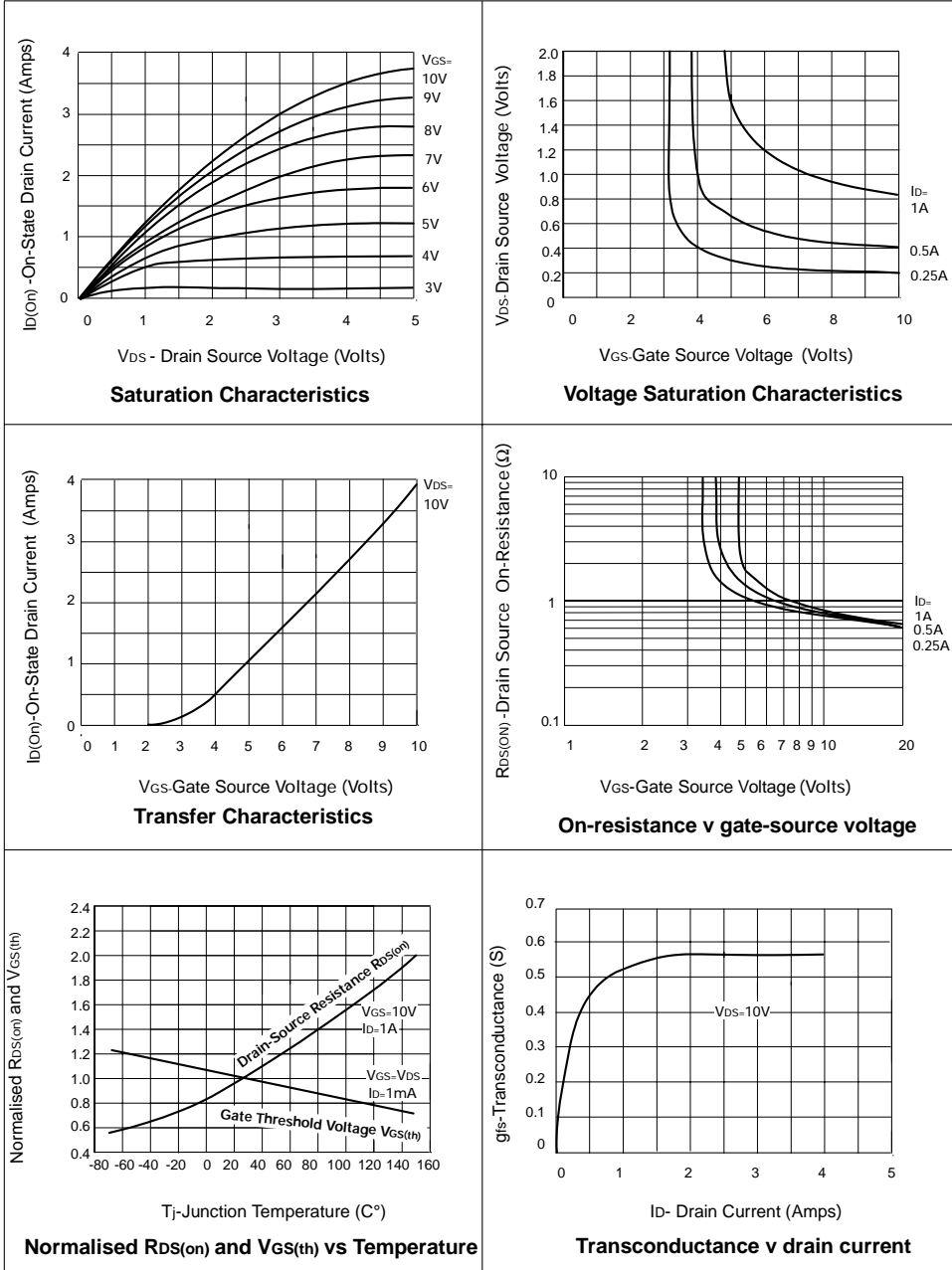


ZVN2106A

TYPICAL CHARACTERISTICS



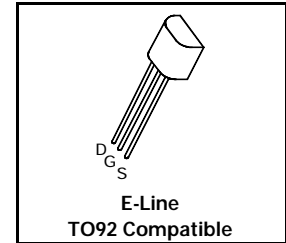
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN2106A

ISSUE 2 – MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}=2\Omega$



ABSOLUTE MAXIMUM RATINGS.

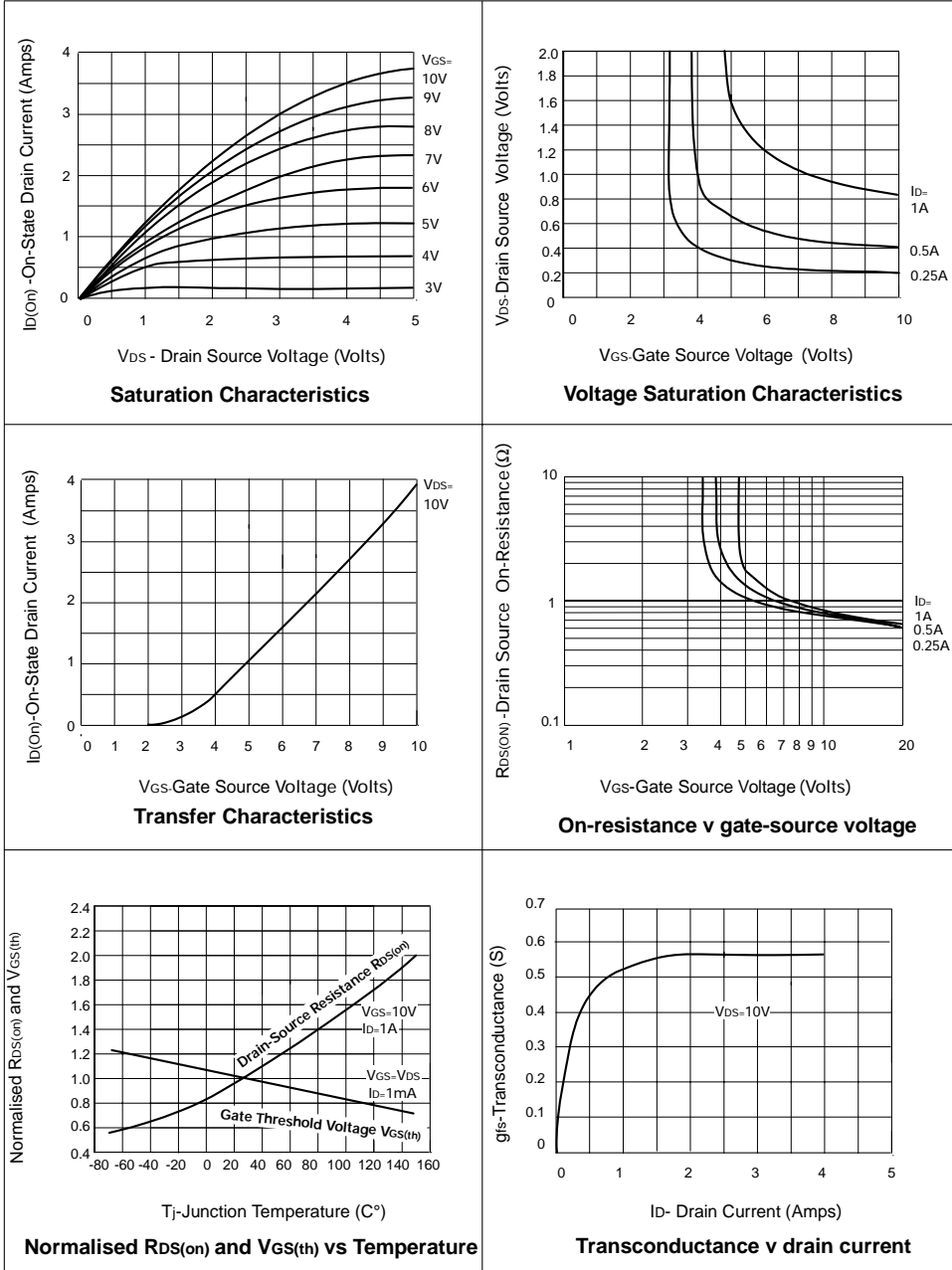
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	450	mA
Pulsed Drain Current	I_{DM}	8	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		500 100	nA μA	$V_{DS}=60V, V_{GS}=0$ $V_{DS}=48V, V_{GS}=0V,$ $T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2		A	$V_{DS}=18V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2	Ω	$V_{GS}=10V, I_D=1A$
Forward Transconductance (1)(2)	g_{fs}	300		mS	$V_{DS}=18V, I_D=1A$
Input Capacitance (2)	C_{iss}		75	pF	$V_{DS}=18V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		45	pF	
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	

ZVN2106A

TYPICAL CHARACTERISTICS



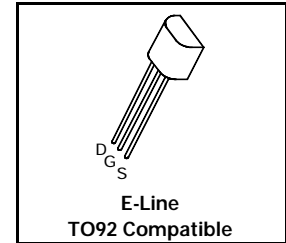
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN2106A

ISSUE 2 – MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)}=2\Omega$



ABSOLUTE MAXIMUM RATINGS.

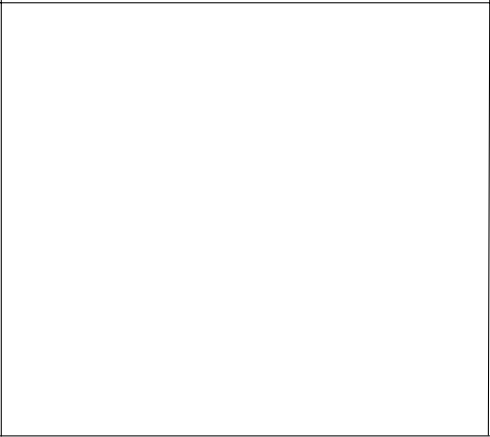
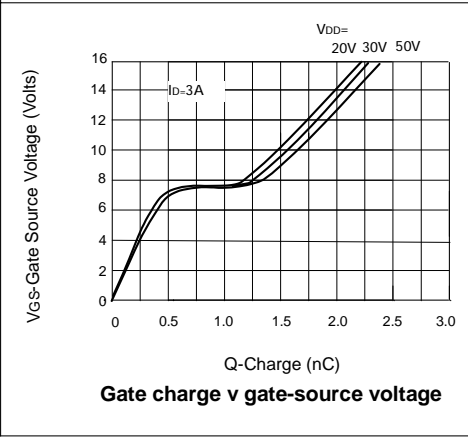
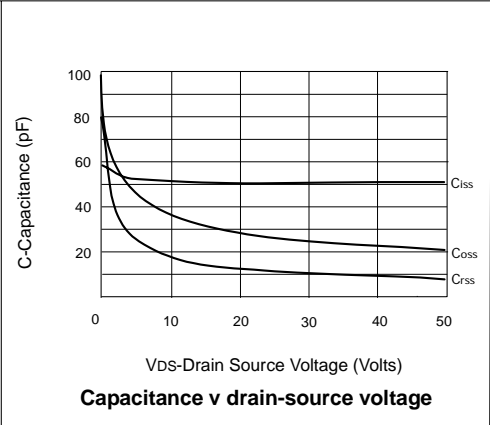
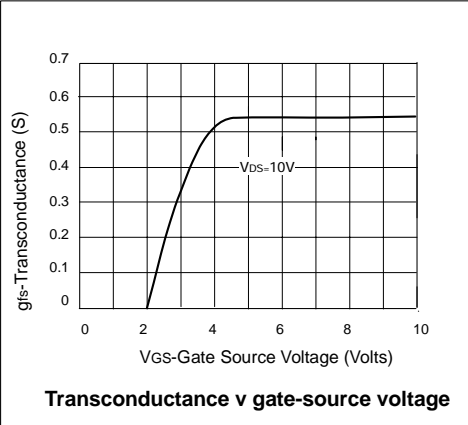
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	450	mA
Pulsed Drain Current	I_{DM}	8	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	700	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		500 100	nA μA	$V_{DS}=60V, V_{GS}=0V$ $V_{DS}=48V, V_{GS}=0V, T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2		A	$V_{DS}=18V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2	Ω	$V_{GS}=10V, I_D=1A$
Forward Transconductance (1)(2)	g_{fs}	300		mS	$V_{DS}=18V, I_D=1A$
Input Capacitance (2)	C_{iss}		75	pF	$V_{DS}=18V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		45	pF	
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	

ZVN2106A

TYPICAL CHARACTERISTICS



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Diodes Incorporated](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#)
[026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#) [IPS70R2K0CEAKMA1](#)
[RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#) [NTE6400](#) [JANTX2N6796U](#)
[JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#) [2SK2614\(TE16L1,Q\)](#)